# Theoretical Study of Thermally Stable Large-Coupling SH<sub>0</sub> Plate Wave Resonators

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Abstract—The thermal stabilization techniques for the fundamental (SH<sub>0</sub>) Plate acoustic wave (PAW) resonators based on LiNbO<sub>3</sub> are theoretically investigated in this paper. The SH<sub>0</sub> mode offers an ultra-large coupling coefficient  $(k^2)$  at a certain crystal cut angle and normalized plate thickness, but its poor temperature coefficient of frequency (TCF) hinders its application in RF systems and needs further improvement urgently. By adding SiO<sub>2</sub> with positive TCF to the LiNbO<sub>3</sub> plate, a robust temperature compensation approach can be achieved for the SH<sub>0</sub> resonators on LiNbO<sub>3</sub>/SiO<sub>2</sub> bilayer and SiO<sub>2</sub>/LiNbO<sub>3</sub>/SiO<sub>2</sub> sandwiched structures. The propagation characteristics of the SH<sub>0</sub> wave propagating in the layered medium are carefully investigated. Despite the trade-off between TCF and  $k^2$ , the SiO<sub>2</sub>/LiNbO<sub>3</sub>/SiO<sub>2</sub> structure provides large  $k^2$ and near-zero TCF for wider thickness combinations. Furthermore, the periodic structure dispersion of the simplest zero-TCF stack is provided and the critical threshold IDT thickness is given.

# Keywords—Lithium niobate, piezoelectricity, resonators, temperature coefficient of frequency (TCF), thermal stability.

#### I. INTRODUCTION

In response to the drastically increasing demands for ubiquitous wireless connectivity, faster data delivery in wireless mobile, Internet-of-Things (IoT), autonomous vehicles, and artificial intelligence, new services currently go into operation requiring progressively wider frequency bands. The coupling coefficient ( $k^2$ ) of the commercially popular surface acoustic wave (SAW) or bulk acoustic wave (BAW) technology is between 6%-13%, limiting the filter bandwidth (*BW*) to up to 6%. Both the current bands wider than 6% with tight specifications and the ultra-wide band (> 15%) required by the next-generation re-configurable filters and cognitive radios point the urgent need of micro-acoustic resonators with ultra-large  $k^2$  [1]-[3].

A LiNbO<sub>3</sub> plate based SH<sub>0</sub> Plate Acoustic Wave (PAW) resonator characterizes the largest  $k^2$  among all acoustic wave devices, up to 50% in certain cut angles and LiNbO<sub>3</sub> thickness [1]. As a result, the SH<sub>0</sub> PAW technology can be an excellent solution to the ultra-wide bands, as well as recently proposed XBARs [4]. However, LiNbO<sub>3</sub> features a material property of drastically softening when temperature rises, leading to very poor temperature coefficient of frequency (*TCF*) of ~ -70 ppm/°C. This poor *TCF* would be unacceptable for any application in current or future RF systems. So an improvement of the thermal stability of LiNbO<sub>3</sub>-based SH<sub>0</sub>

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resonators is highly desirable for enabling low-temperaturedrift and ultra-wide-band filters [5].

The thermal stability can be achieved by adding SiO<sub>2</sub>, which has a positive *TCF* of ~ +80 ppm/°C to the LiNbO<sub>3</sub> plate, forming a robust passive compensation. The SH<sub>0</sub> wave propagation characteristics are carefully investigated after introducing the non-piezoelectric SiO<sub>2</sub> herein and optimized stack proposed for achieving the thermal insensitivity and large  $k^2$  simultaneously. Moreover, the periodic structure dispersion of the simplest zero-*TCF* stack is provided.



Fig. 1. Calculated (a) phase velocity and (b) first-order *TCV* versus rotation angle of the first six Plate modes in the rotated *YX* LiNbO<sub>3</sub> membrane  $(h_{LiNbO3}/\lambda=0.1)$  when the mechanical loading of IDT is ignored  $(h_{IDT}=0)$ .



Fig. 2. Calculated (a)  $f - \beta$  dispersion curve and (b) dispersive  $k^2$  of the first six Plate modes in the 30° YX LiNbO<sub>3</sub> membrane ( $h_{IDT} = 0$ ).

#### II. SH<sub>0</sub> PLATE WAVE PROPAGATING IN LINBO<sub>3</sub> MEMBRANE

## A. Cut Angle

Fig. 1 (a) and (b) show the  $k^2$  and temperature coefficient of velocity (*TCV*) across all rotation angle from the *YX* LiNbO<sub>3</sub> for the first six Plate modes with  $h_{LiNbO3}/\lambda = 0.1$  ( $\lambda$  is twice the IDT pitch). The  $k^2$  varies largely due to the prominent anisotropy of the piezoelectric matrix, so the optimal cut angle can be chosen so as to optimize the  $k^2$ . The peak  $k^2$  of 55% happens at rotation angle of ~30° with Euler angle (0°,120°,0°). It is also interesting to note that at this rotation angle of around 30°, the  $k^2$ 's of most other Plate modes are minimized, especially the A<sub>1</sub> Lamb mode that is outstanding around Z-cut.

The *TCV* can be derived from the temperature coefficients of elasticities (*TCE*'s) and temperature dependence of density of LiNbO<sub>3</sub> [7]. By adding the effect of *TCV* together with the thermal expansion coefficient ( $\alpha$ ), *TCF* can be estimated as:

$$TCF_{1st} = \frac{1}{f} \frac{\partial f}{T} = \frac{1}{v} \frac{\partial v}{T} - \alpha_x = TCV_{1st} - \alpha_x$$
(1)

The  $\alpha_x$  of LiNbO<sub>3</sub> is around 15.4 ppm/°C so that the LiNbO<sub>3</sub> plate based resonators show very poor intrinsic *TCF* of

-60—100 ppm/°C. Luckily at the rotation angle of ~ 30° the *TCV* of the SH<sub>0</sub> mode is minimized across the entire cut angle.

#### B. Dispersion

The dispersion characteristics of the first six Plate waves propagating in the 30° YX LiNbO<sub>3</sub> with  $h_{LiNbO3}/\lambda = 0.1$  are shown in Fig. 2 (a). The normalized wave number of the x axis corresponds to normalized LiNbO<sub>3</sub> plate thickness:

$$\frac{\beta \cdot h_{LiNbO3}}{2\pi} = \frac{h_{LiNbO3}}{\lambda} \cdot$$
(2)

Evidently, the  $SH_0$  mode shows weakest dispersion and features the advantage of pitch-controlled frequency even when the LiNbO<sub>3</sub> plate thickness approaches zero. In addition, the low dispersion of the fundamental modes also allows the agile design of the acoustic-coupled filters [6].

Fig. 2 (b) depicts the dispersive  $k^2$  of the first six Plate waves for the single-IDT transducer configuration in the 30° *YX* LiNbO<sub>3</sub>. At this cut angle of (0°,120°,0°), the SH<sub>0</sub> mode features very large  $k^2$  while the other modes are suppressed. Especially when LiNbO<sub>3</sub> is thin (< 0.2 $\lambda$ ), the  $k^2$  is higher than 40% and clean wide-band spectrum is expected.

#### III. SH<sub>0</sub> WAVE CHARACTERISTICS IN LINBO<sub>3</sub>/SIO<sub>2</sub> and SIO<sub>2</sub>/LINBO<sub>3</sub>/SIO<sub>2</sub>

#### A. Phase Velocity Degradation

The piezoelectric-dead SiO<sub>2</sub> layer loads the LiNbO<sub>3</sub> thin film and significantly reduces the phase velocity ( $v_p$ ) of the SH<sub>0</sub> mode in the LiNbO<sub>3</sub>/SiO<sub>2</sub> membrane, as shown in Fig. 3. The  $v_p$  of the SH<sub>0</sub> mode in the symmetrical SiO<sub>2</sub>/LiNbO<sub>3</sub>/SiO<sub>2</sub> membrane is higher than that in the LiNbO<sub>3</sub>/SiO<sub>2</sub> bilayer structure, especially when the thicker SiO<sub>2</sub> layer is utilized and  $h_{\text{LiNbO3}}/\lambda$  is small. At thin LiNbO<sub>3</sub> with  $h_{LiNbO3}/\lambda = 0.1$  the SH<sub>0</sub> mode in the SiO<sub>2</sub>/ LiNbO<sub>3</sub>/SiO<sub>2</sub> membrane shows the phase velocity of roughly 4,280 m/s and in the LiNbO<sub>3</sub>/SiO<sub>2</sub> bilayer structure around 4,200 m/s at  $h_{\text{SiO2}}/\lambda = 0.2$ .



Fig. 3. Comparison of the FEA simulated  $v_p$  dispersion of the SH<sub>0</sub> mode in the LiNbO<sub>3</sub>/SiO<sub>2</sub> bilayer membrane and in the symmetrical SiO<sub>2</sub>/LiNbO<sub>3</sub>/SiO<sub>2</sub> composite membrane with 30° *YX* LiNbO<sub>3</sub>.



Fig. 4. Comparison of the FEA simulated  $k^2$  dispersion utilizing the SH<sub>0</sub> mode in the LiNbO<sub>3</sub>/SiO<sub>2</sub> bilayer membrane and in the symmetrical SiO<sub>2</sub>/ LiNbO<sub>3</sub>/SiO<sub>2</sub> composite membrane with (a) single-IDT and (b) double-IDT.

## B. Coupling Coefficient Degradation

As depicted in Fig. 4, the  $k^2$  dispersion curves of the SH<sub>0</sub> mode on the LiNbO<sub>3</sub>/SiO<sub>2</sub> and SiO<sub>2</sub>/LiNbO<sub>3</sub>/SiO<sub>2</sub> composite membrane are compared with single-IDT and double-IDT transducer configurations. The  $k^2$  is usually deteriorated by the additional SiO<sub>2</sub> layer because of the acoustic energy absorption by the piezo-dead and soft SiO<sub>2</sub> layer. Since the acoustic wave field tends to be more involved in the LiNbO<sub>3</sub> layer of the symmetrical SiO<sub>2</sub>/LiNbO<sub>3</sub>/SiO<sub>2</sub> plate, the acoustic energy can be confined in the LiNbO<sub>3</sub> plate to enable a higher  $k^2$  for the SH<sub>0</sub> mode. As a result, especially when thick SiO<sub>2</sub> layers are employed, the  $k^2$  of the SH<sub>0</sub> mode in the SiO<sub>2</sub>/LiNbO<sub>3</sub>/SiO<sub>2</sub> sandwiched plate is larger than in the LiNbO<sub>3</sub>/SiO<sub>2</sub>.

Intriguingly, for some cases the  $k^2$  of the SH<sub>0</sub> mode in the layered plates can be even larger than that in the LiNbO<sub>3</sub> single plate. For example when  $h_{LiNbO3}/\lambda = 0.3-1$  is employed for double-IDT and double-SiO<sub>2</sub>, the  $k^2$  is much increased, where the growing contribution of the  $e_{15}$  piezoelectric constant by the surface constraint overcomes the loading effect.

#### C. TCF and Trade-Off

Neglecting the electrode thickness, the first-order *TCF*'s of the LiNbO<sub>3</sub>/SiO<sub>2</sub> and SiO<sub>2</sub>/LiNbO<sub>3</sub>/SiO<sub>2</sub> SH<sub>0</sub> resonators can be theoretically predicted and are depicted in dashed lines of Fig. 5 and Fig. 6. By adding the SiO<sub>2</sub> layers onto the LiNbO<sub>3</sub> thin film, the *TCF*'s increase fast and cross 0 ppm/C°. However, the first-order *TCF*'s in the SiO<sub>2</sub>/LiNbO<sub>3</sub>/SiO<sub>2</sub> plate are slightly smaller than in the LiNbO<sub>3</sub>/SiO<sub>2</sub> plate at the same  $h_{LiNbO3}/\lambda$  and  $h_{SiO2}/\lambda$ , giving opposite preference for selecting stack configuration from considering  $v_p$  and  $k^2$ . In addition, there is also a general trade-off relation between the *TCF* and  $k^2$  for selecting the stack thicknesses.

In order to compare the trade-offs, the  $k^2$  values at zero *TCF* are identified and marked in dots in Fig. 5 and Fig.6. In general, the SH<sub>0</sub> mode in the sandwiched structure still offers a slightly larger  $k^2$  than in the bilayer plate, especially at greater LiNbO<sub>3</sub> thicknesses. The simplest zero-*TCF* stack can be LiNbO<sub>3</sub>/SiO<sub>2</sub> with  $h_{LiNbO3}/\lambda = 0.1$ ,  $h_{SiO2}/\lambda = 0.2$ , and single-IDT. It is also interesting to notice that for double-IDT and double-SiO<sub>2</sub> the  $k^2$  can be large (~30%) even at a thicker LiNbO<sub>3</sub> at zero-*TCF*, showing potential for the multi-frequency application (large pitch variation in the same stack).



Fig. 5 Trade-off between the first-order  $TCF_{1st}$  and intrinsic  $k^2$  of the SH<sub>0</sub> mode in the LiNbO<sub>3</sub>/SiO<sub>2</sub> bi-layer structure and symmetrical SiO<sub>2</sub>/LiNbO<sub>3</sub>/SiO<sub>2</sub> composite membrane with single-IDT transducer.



Fig. 6. Trade-off between the first-order *TCF* and intrinsic  $k^2$  of the SH<sub>0</sub> mode in the LiNbO<sub>3</sub>/SiO<sub>2</sub> bi-layer structure and symmetrical SiO<sub>2</sub>/LiNbO<sub>3</sub>/SiO<sub>2</sub> composite membrane with double-IDT transducer.

#### IV. DISPERSION

The periodically perturbed dispersion of the SH<sub>0</sub> wave propagating in LiNbO<sub>3</sub> membrane determined by the presence of a frequency stopband [8] will be impacted by adding the SiO<sub>2</sub> layer. The open-circuited (OC) dispersion analysis of the SH<sub>0</sub> wave travelling in the LiNbO<sub>3</sub>/SiO<sub>2</sub> bilayer structure with near-zero TCF ( $h_{LiNbO3}/\lambda = 0.1$  and  $h_{SiO2}/\lambda = 0.2$ ) is provided in Fig. 7. For the OC boundary condition, the non-excited modes appear in the lower stopband edge when IDT is relatively thin  $(h_{IDT}/\lambda = 4\%$  and  $h_{IDT}/\lambda = 6\%$ ) and start to be at the upper stopband edge when the IDTs become thicker  $(h_{IDT}/\lambda)$  > 6%). The phenomenon of the non-excited mode below the OC excitable mode  $(f_p)$  is rare and detrimental to the passband performance. In this case, the short-circuited (SC) reflection coefficient is not enough to cover the OC excitable mode, and the OC reflection coefficient is negative. As a result, it is critical to use thicker IDT electrodes for the SH<sub>0</sub> resonators.

# V. CONCLUSIONS

The thermal stabilization techniques for the  $SH_0$  mode in  $LiNbO_3$  PAW resonators is investigated using the  $LiNbO_3/SiO_2$  and  $SiO_2/LiNbO_3/SiO_2$  structures. The  $SiO_2/LiNbO_3/SiO_2$ 



Fig. 7. Real part of the SH<sub>0</sub> propagation constant in single-IDT and opencircuited condition for different electrode thicknesses of the SH<sub>0</sub> mode propagating in the LiNbO<sub>3</sub>/SiO<sub>2</sub> bilayer structure assuming  $\lambda = 1 \mu m$ ,  $h_{LiNbO_3}/\lambda = 0.1$ ,  $h_{SiO_2}/\lambda = 0.2$  and DF = 0.5.

sandwiched membrane enables higher  $v_p$  and larger  $k^2$  than the LiNbO<sub>3</sub>/SiO<sub>2</sub> bilayer since the symmetric structure traps more acoustic field in the LiNbO<sub>3</sub> piezoelectric layer. By considering the trade-off between *TCF* and  $k^2$ , simplest zero-*TCF* stack is proposed as LiNbO<sub>3</sub>/SiO<sub>2</sub> with  $h_{LiNbO_3}/\lambda = 0.1$ ,  $h_{SiO2}/\lambda = 0.2$ , and single-IDT. The dispersive stopband analysis is given for this structure and the threshold IDT thickness of 8% is provided for wide enough stopband *BW* covering passband. Intriguingly, the SiO<sub>2</sub>/LiNbO<sub>3</sub>/SiO<sub>2</sub> structure with double-IDTs offers a wide selection of thickness combinations for simultaneously enabling large  $k^2$  and zero-*TCF*, showing potential for the multi-frequency applications.

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